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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Katsuhida MANABE et al.

Serial No.: 09/783,035 ✓

Group Art Unit: 2813

Filed: February 15, 2002

Examiner: Nguyen, Thanh T.

For: LIGHT-EMITTING SEMICONDUCTOR DEVICE USING GROUP III NITROGEN COMPOUND

Honorable Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated June 28, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 16 as follows:

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16. (Amended) A method for producing a light-emitting semiconductor device, said method comprising:

- forming a substrate; G
- forming a buffer layer on said substrate;
- forming an N-layer nitrogen-III Group compound semiconductor satisfying the formula $Al_xGa_yIn_{1-x-y}N$, inclusive of $x=0$, $y=0$, and $x=y=0$;
- forming a P-layer of P-type nitrogen-III Group compound semiconductor satisfying the formula $Al_xGa_yIn_{1-x-y}N$, inclusive of $x=0$, $y=0$, and $x=y=0$; and
- forming between said N-layer and said P-layer a middle layer of nitrogen-III Group compound semiconductor satisfying the formula $Al_xGa_yIn_{1-x-y}N$ inclusive of $x=0$, $y=0$, and $x=y=0$, said middle layer being doped with a P-type dopant.